

# FDP7045L/FDB7045L

# N-Channel Logic Level PowerTrench® MOSFET

#### **General Description**

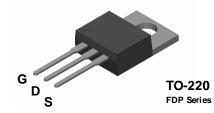
This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

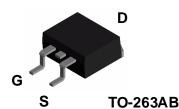
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{\scriptscriptstyle DS(on)}$  specifications resulting in DC/DC power supply designs with higher overall efficiency.

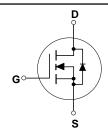
#### **Features**

- 100 A, 30 V.  $R_{DS(ON)}$  = 0.0045  $\Omega$  @  $V_{GS}$  = 10 V  $R_{DS(ON)}$  = 0.006  $\Omega$  @  $V_{GS}$  = 4.5 V.
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance PowerTrench technology for extremely low  $R_{\scriptscriptstyle DS(ON)}.$
- 175°C maximum junction temperature rating.

**FDB Series** 







Absolute Maximum Ratings To = 25°C unless otherwise noted

Absolut	le Maximum Natings 10-23 c dilless offerwise in	I	ı	1					
Symbol	Parameter	FDP7045L	FDB7045L	Units					
V <sub>DSS</sub>	Drain-Source Voltage	;	30	V					
$V_{GSS}$	Gate-Source Voltage	±	20	V					
I <sub>D</sub>	Maximum Drain Current - Continuous (Note 1)	1	00	Α					
		-	75						
	- Pulsed (Note 1)	3	00						
P <sub>D</sub>	Total Power Dissipation @ T <sub>C</sub> = 25°C	1	W						
	Derate above 25°C	0	.85	W/∘C					
$T_J$ , $T_{STG}$	Operating and Storage Junction Temperature Range	-65 to	+175	∘C					
Thermal Characteristics									
		1							

$R_{\theta^{JC}}$	Thermal Resistance, Junction-to-Case	1.2	∘C/W
R <sub>AJA</sub>	Thermal Resistance, Junction-to-Ambient	62.5	∘C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDB7045L	FDB7045L	13"	24mm	800
FDP7045L	FDP7045L	Tube	N/A	45

Symbol	Parameter	Parameter Test Conditions				
Off Char	acteristics			•		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	ain-Source Breakdown $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				V
<u>A</u> BVoss ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		22		mV/∘C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250  \mu A$	1	1.5	3	V
ΔVGS(th)	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to 25°C		-5		mV/°C
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 50 \text{ A},$ $V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 40 \text{ A}$		0.0039 0.0056 0.0048	0.0045 0.0070 0.0060	Ω
I <sub>D(on)</sub>	On-State Drain Current	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 10 V	50			Α
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 50 \text{ A}$		120		S
Dynamic	Characteristics			•		
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		5400		pF
Coss	Output Capacitance	f = 1.0 MHz		1170		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			530		pF
Switchin	q Characteristics (Note 2)	l		I		
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 50 \text{ A},$		14	30	ns
t <sub>r</sub>	Turn-On Rise Time	V <sub>GS</sub> = 10 V		114	160	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			105	150	ns
t <sub>f</sub>	Turn-Off Fall Time			115	160	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 15 V,		50	70	nC
$Q_{gs}$	Gate-Source Charge	$I_D = 50 \text{ A}, V_{GS} = 5 \text{ V}$		16		nC
$Q_{gd}$	Gate-Drain Charge			16		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings				
l <sub>s</sub>	Maximum Continuous Drain-Source				75	Α
V <sub>SD</sub>	Drain-Source Diode Forward	V = 0 V, I = 50 A (Note 2)		0.95	1.2	V

Notes:

1. Calculated continuous current based on maximum allowable junction temperature. Actual maximum continuous current limited by package constraints to 75A.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

### **Typical Characteristics**

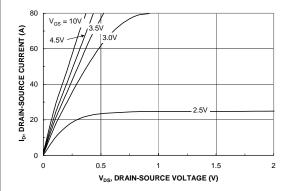


Figure 1. On-Region Characteristics.

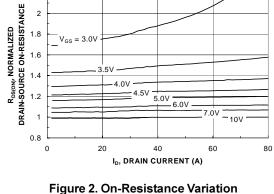


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

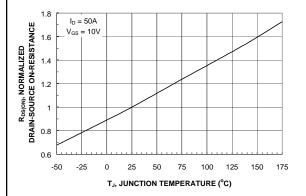


Figure 3. On-Resistance Variation with Temperature.

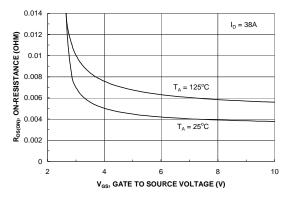


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

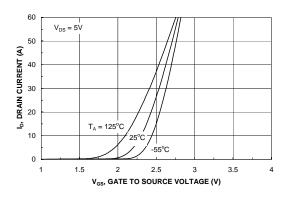


Figure 5. Transfer Characteristics.

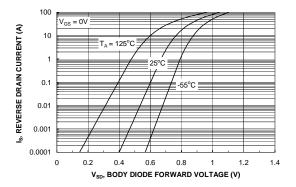
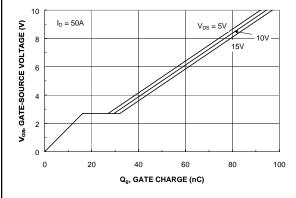


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### Typical Characteristics (continued)



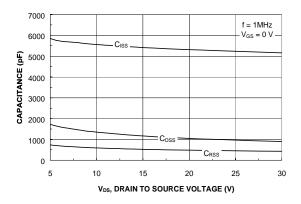
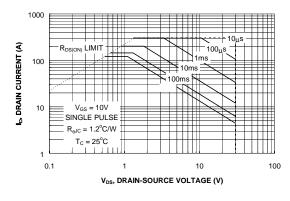


Figure 7. Gate-Charge Characteristics.





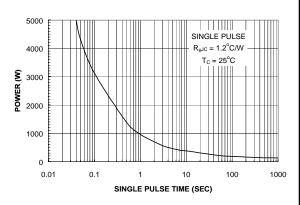


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

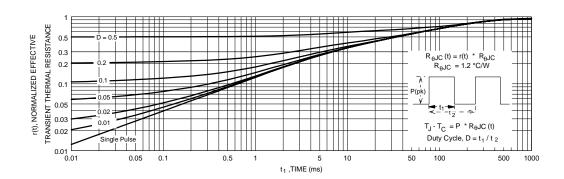
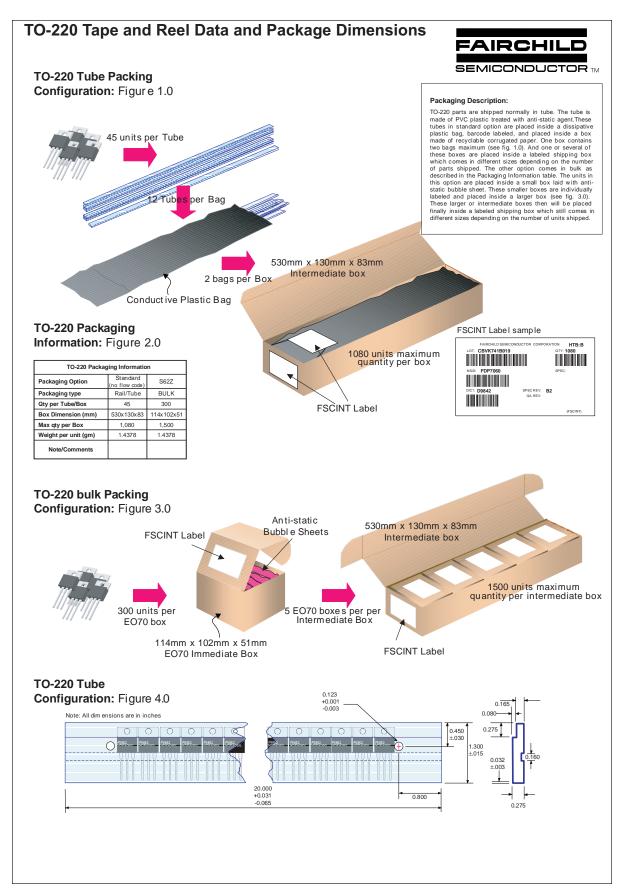


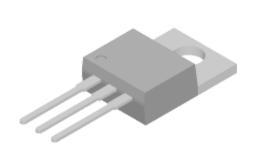
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient themal response will change depending on the circuit board design.

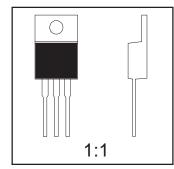


## TO-220 Tape and Reel Data and Package Dimensions, continued

# TO-220 (FS PKG Code 37)

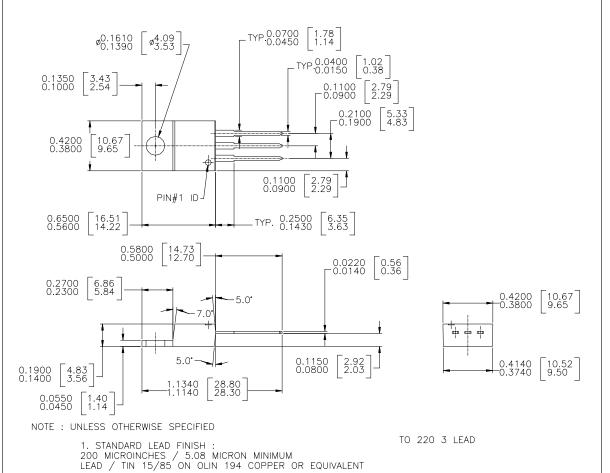


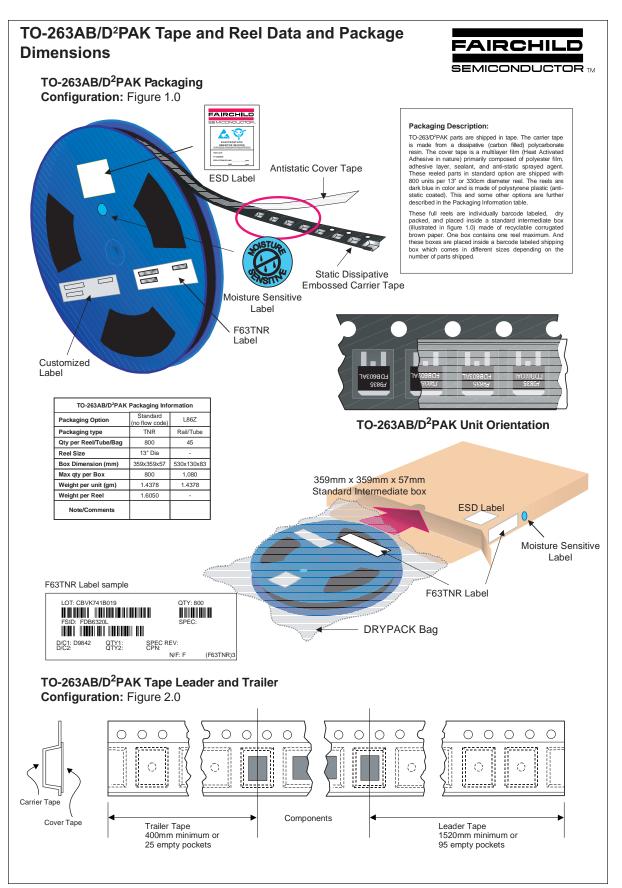
2. DIMENSION BASED ON JEDEC STANDARD TO-220 VARIATION AB, ISSUE J, DATED 3/24/87



Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

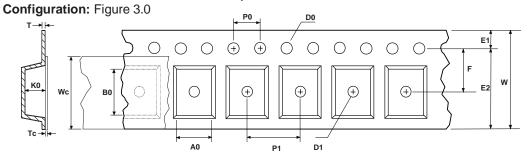
Part Weight per unit (gram): 1.4378





# TO-263AB/D<sup>2</sup>PAK Tape and Reel Data and Package Dimensions, continued

### TO-263AB/D<sup>2</sup>PAK Embossed Carrier Tape



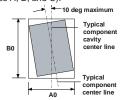
# User Direction of Feed

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
TO263AB/ D²PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

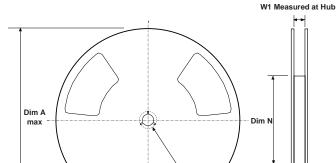


Sketch B (Top View)
Component Rotation

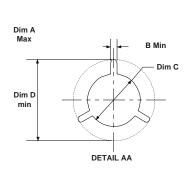


Sketch C (Top View)
Component lateral movement

# **TO-263AB/D<sup>2</sup>PAK Reel Configuration:** Figure 4.0







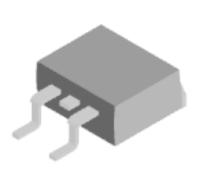
W2 max Measured at Hub

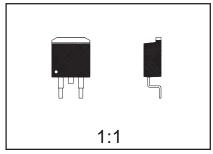
See detail AA

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

## TO-263AB/D<sup>2</sup>PAK Tape and Reel Data and Package Dimensions, continued

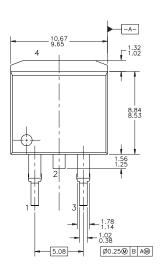
# TO-263AB/D<sup>2</sup>PAK (FS PKG Code 45)

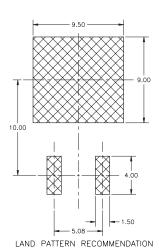


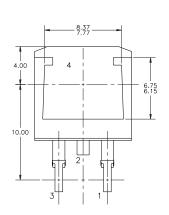


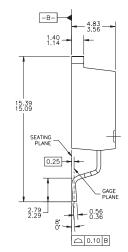
Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 1.4378









- NOTES: UNLESS OTHERWISE SPECIFIED

  A) ALL DIMENSIONS ARE IN MILLIMETERS.
  B) STANDARD LEAD FINISH:
  200 MICROINCHES / 5.08 MICROMETERS MIN.
  LEAD/TIN 15/85 ON OLIN 194 COPPER OR
  EQUIVALENT.
  C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
  TO EXCEED 0.003 INCH / 0.05mm.
  D) NO PACKAGE CHIPS, CRACKS OR SURFACE
  IDENTIFICATION ALLOWED AFTER FORMING.
  E) REFERENCE JEDEC, TO—265, ISSUE C,
  VARIATION AB, DATED 2/92.

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 $\begin{array}{lll} \mathsf{FAST}^{\circledast} & \mathsf{Quiet}\,\mathsf{Series^{\mathsf{TM}}} \\ \mathsf{FASTr^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}\text{-}3} \\ \mathsf{GTO^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}\text{-}6} \\ \mathsf{HiSeC^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}\text{-}8} \\ \end{array}$ 

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition			
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.			
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.			
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.			
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.			